

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

2SK3745LS— High-Voltage, High-Speed Switching Applications

Features

- · Low ON-resistance, low input capacitance, ultrahigh-speed switching
- · High reliability (Adoption of HVP process)
- · Micaless package facilitating mounting
- · Avalanche resistance guarantee

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		1500	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	ID*		2	А
Drain Current (Pulse)	IDP		4	А
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C	35	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		41	mJ
Avalanche Current *2	IAV		2	А

^{*}Shows chip capability

Package Dimensions

unit : mm (typ) 7528-001

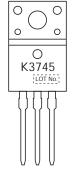
Product & Package Information

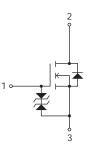
• Package : TO-220F-3FS

• JEITA, JEDEC : SC-67

• Minimum Packing Quantity: 50 pcs./magazine

Marking Electrical Connection





SANYO Semiconductor Co., Ltd.

^{*1} V_{DD}=50V, L=20mH, I_{AV}=2A (Fig.1)

^{*2} L≤20mH, single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	1500			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =1200V, V _{GS} =0V			100	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2.5		3.5	V
Forward Transfer Admittance	yfs	V _{DS} =20V, I _D =1A	0.7	1.4		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =1A, V _G S=10V		10	13	Ω
Input Capacitance	Ciss			380		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		70		pF
Reverse Transfer Capacitance	Crss			40		pF
Turn-ON Delay Time	t _d (on)			12		ns
Rise Time	t _r	Son Fig 2		37		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		152		ns
Fall Time	tf			59		ns
Total Gate Charge	Qg			37.5		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =2A		2.7		nC
Gate-to-Drain "Miller" Charge	Qgd			20		nC
Diode Forward Voltage	V _{SD}	I _S =2A, V _{GS} =0V		0.88	1.2	V

Fig.1 Avalanche Resistance Test Circuit

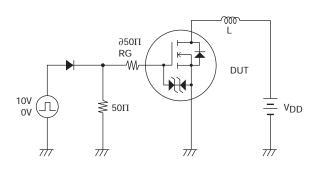
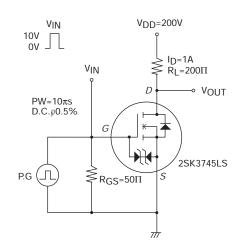
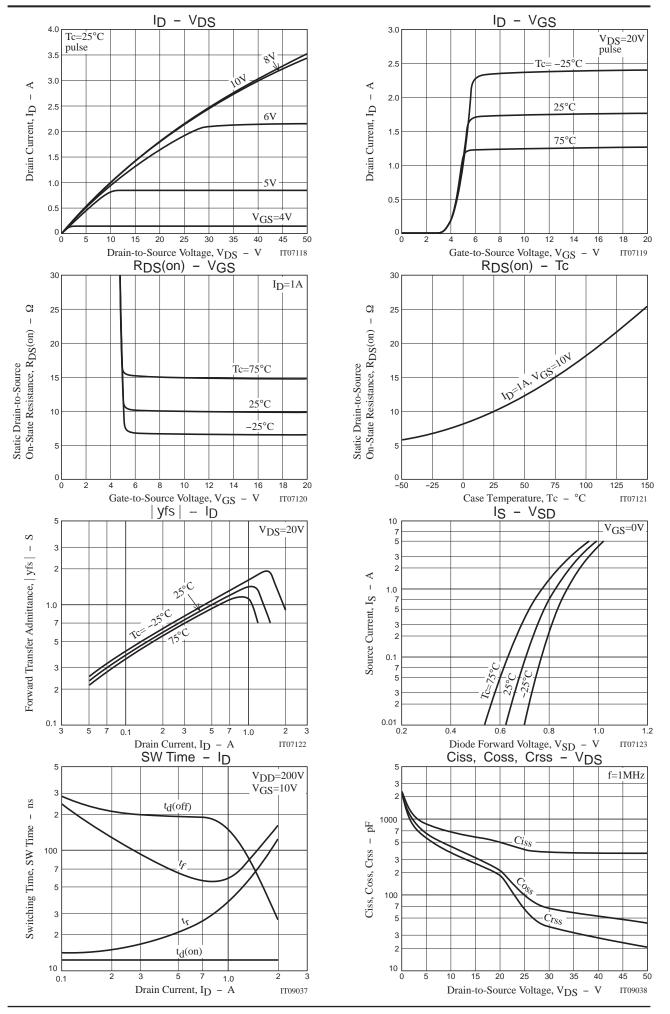


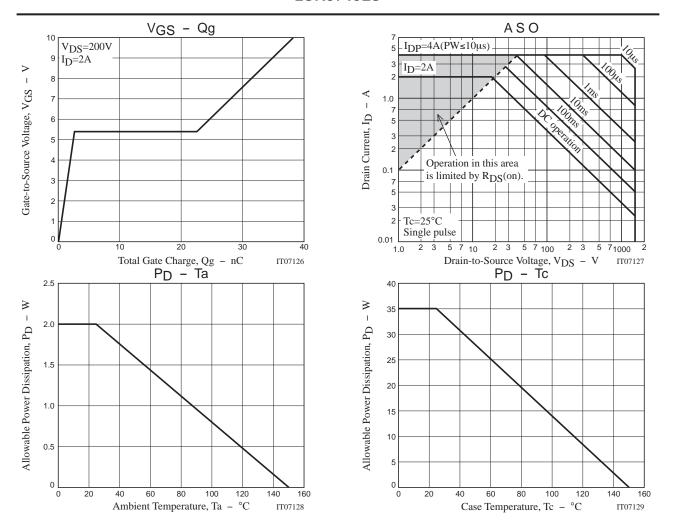
Fig.2 Switching Time Test Circuit



Ordering Information

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Device	Package	Shipping	memo
2SK3745LS-1E	TO-220F-3FS	50pcs./magazine	Pb Free



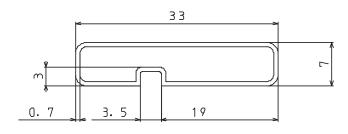


Magazine Specification

2SK3745LS-1E

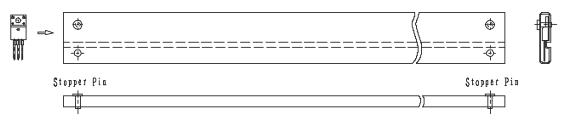
1. Packing Format

Package Name	Magagine Name	Maximum Number of devices contained (pcs) Magazine Name Inner box Outer box		Packing format		
1 4 4 4 4 4 1 4 4 4 4	Idag as the Hams			Outer box	Inner BOX	Outer BOX
TO-220F-3F\$	TO-220F	50	1, 000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm (external) 590×225×178

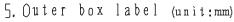


Tolerance=±(), 3mm
Thickness=(), 7±(), 2mm
Length =532, 5±2mm
Material =PVC (Antistatic treatment)

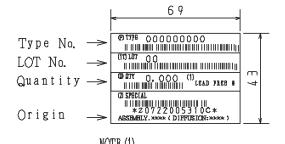
3. Storage method to magazine

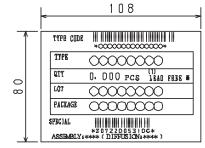


4. Inner box label (unit:mm)



It is a label at the time of factory shigments. The form of a label may change in physical distribution process.



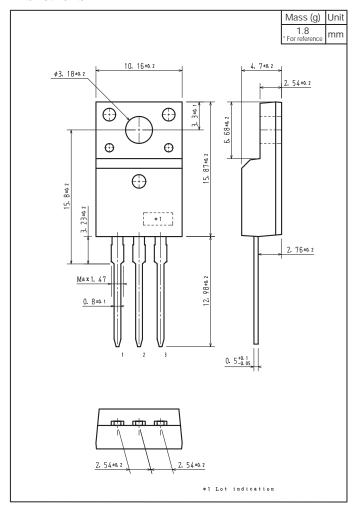


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

Outline Drawing

2SK3745LS-1E



Note on usage: Since the 2SK3745LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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